

SAED 90
Device Parameters

Device nmos12

tox	2.05	nm
Vth0	397	mV
Idsat (Lmin)	869	uA/um
unCox (long)	428	uA/V ²
Xj	15	nm
Gamma	0.4	V ^{0.5}
Cov	0.26	fF/um
CJ	0.5	fF/um ²
CJSW	0.5	fF/um

Device pmos12

tox	2.15	nm
Vth0	-276	mV
Idsat (Lmin)	-426	uA/um
upCox (long)	-124	uA/V ²
Xj	28	nm
Gamma	0.4	V ^{0.5}
Cov	0.26	fF/um
CJ	0.5	fF/um ²
CJSW	0.5	fF/um